Max. Marks: 50

2063

B.E. (Electronics and Communication Engineering) Third Semester

Time allowed: 3 Hours

EC-307: Electronics Devices and Circuits

NOTE: Attempt five questions in all, including Question No. I which is compulsory and selecting two questions from each Part. 1. Attempt the following:-(a) Define operating point or quiescent point of transistor. (1) (b) How FET can be employed as a variable resistor? (1) (c) Sketch the basic construction of a n-channel depletion-type MOSFET. (1) (d) What is an emitter follower? When it is used? (1) (e) Define transconductance (g_m) parameter of a FET transistor. (1) (f) What is meant by amplifier distortion? (1)(g) Discuss diode compensation for V_{BE}. (1) (h) List stabilization techniques for a transistor. (1)(i) What is the significant difference between the construction of an enhancement-type MOSFET and a depletion-type MOSFET? (1) (i) Briefly discuss condition for thermal stability. (1) PART-A 2. a) Derive current voltage equation of enhancement type NMOS transistor. (5) b) Derive transconductance (g_m) equation for JFET. (5) 3. a) How JFET is different from MOS transistor? What are typical applications of MOS transistors? Discuss voltage divider biasing technique in JFET. (5) b) Discuss hybrid parameters of BJT. How they are helpful in analysis of transistor (5)amplifiers. 4. Explain in detail stabilization against variations in I_C, V_{BE} , and β for a BJT transistor. (10) PART-B 5. (a) Discuss operation of complementary symmetry push-pull amplifiers. (5)(b) What advantages are offered by negative feedback? Explain different types of (5)feedback connections that can be used in amplifiers or oscillators. $(2.5 \times 4 = 10)$ 6. Write short note on following a) Cascode Circuit b) Colpitt's Oscillator c) Class-C Amplifier d) RC coupled amplifier 7. Discuss low and high frequency response of BJT. What parameters play important role is (10)frequency response of BJT?